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Appl. No. 09/639,636
Amdt. Dated 5 December 2003
Reply to Office action of 10 October 2003

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Appl. No.	:	09/639,636
Applicant	:	Guida et al.
Filed	:	15 August 2000
Title	:	High Resolution Anti-Scatter X-ray Grid and Laser Fabrication Method
TC/A.U.	:	1722
Examiner	:	Luk, Emmanuel S.
Docket No.	:	RD25905-6
Customer No.	:	6147

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RESPONSE UNDER 37 CFR 1.116

This case has been carefully reviewed in light of the Final Office Action dated 10 October 2003, wherein claims 10-11 and 15-17 were rejected under 35 USC 103(a) on Lambda Physik Industrial Report; claim 12 was rejected under 35 USC 103(a) on Lambda Physik Industrial Report in view of Konishi, US Patent No. 6,034,825; and claims 18-21 were rejected under 35 USC 103(a) on Lambda Physik Industrial Report in view of Guida et al., US Patent No. 5,557,650.

Claims 10-12 and 15-21 remain pending in this application. Reconsideration in light of the following remarks is respectfully requested.

Claims 10-11 and 15-17

Applicants respectfully traverse the rejection of claims 10-11 and 15-17 under 35 USC 103(a) over Lambda Physik Industrial Report. Applicants respectfully submit that Lambda does not teach or disclose the claim 10 recitations of (with emphasis added):

Claim 10 (previously presented). A system for patterning a substantially transparent polymer substrate of an anti-scatter x-ray grid, the system comprising:
a high power laser for providing laser light;
a beam homogenizer for conditioning the laser light; and
a phase mask for creating a pattern of the conditioned laser light while reducing an amount of the conditioned laser light which is lost to the phase mask;
the laser, the beam homogenizer, and the phase mask being positioned for ablating openings having slopes less than or equal to 0.25 degrees and extending completely through an anti-scatter x-ray grid substrate having a thickness ranging from 0.3 millimeters to 1.5 millimeters.

Neither of the Lambda reference examples relate to x-ray grid substrates. One example relates to via formation (pages 1-6), and the other relates to ink jet nozzles (pages 6-8).

Pages 1-6 of the Lambda reference describes conventional via formation for electronic packaging applications with wall angle ranges described as 50-65 degrees for 1987 and 20-75 degrees for 1994 (page 3, table 2) and shows wall angles in FIGs. 10 and 11 that are necessary for metal coverage (bottom left of page 5).